

- Drafts
- Pending
- Active
  - L1: (43) (((barrier near (height tunnel)) tunnel\$4 ((energy diagram
  - Failed
  - Saved
    - S1: (1) 09/848877
    - S2: (1738) "KONINKLIJKE PHILIPS".as.
    - S3: (175943) ((barrier near (height tunnel)) tunnel\$4 ((energy diagram
    - S4: (39120) ((barrier near (height tunnel\$4)) ((energy diagram cond
    - S5: (6062820) different second
    - S6: (1448) (different second) adj (((barrier near (height tunnel\$4)) ((
    - S7: (43918) float\$4 adj (gate electrode plate trap\$4) FG
    - S8: (187632) (control adj) (gate electrode plate) CG word adj line wordli
    - S9: (8) ((different second) adj (((barrier near (height tunnel\$4)) ((en
    - S10: (11) ((different second) adj (((barrier near (height tunnel\$4)) ((
    - S11: (14) ((different second) adj (((barrier near (height tunnel\$4)) ((
    - S12: (5) ((different second) adj (((barrier near (height tunnel\$4)) ((
    - S13: (9) ((different second) adj (((barrier near (height tunnel\$4)) ((
    - S14: (4) ("6461931" "6586797").pn.
    - S15: (26007) micron.as.
    - S16: (71272) erase
    - S17: (295786) retain\$4
    - S18: (46938) (float\$4 adj (gate electrode plate trap\$4) FG)

(((barrier near (height tunnel)) tunnel\$4 ((energy diagram conduct\$4 gap width) near band) bandgap bandwidth (work adj function) )  
 ) near6 erase same (( float\$4 adj (gate electrode plate trap\$4) FG)  
 )) same (((barrier near (height tunnel)) tunnel\$4 ((energy diagram conduct\$4 gap width) near band) bandgap bandwidth (work adj function) )  
 ) near6 retain\$4)

Feb, 2023

| U  | Inventor  | Document Issue P | Title            | Current                             | X                                   | Retrieval                           | S                                   | C                                   | P                                   | Image                               | Do        | P |
|----|---|------------------|------------------|-------------------------------------|-------------------------------------|-------------------------------------|-------------------------------------|-------------------------------------|-------------------------------------|-------------------------------------|-----------|---|
| 1  | <input checked="" type="checkbox"/> Chindalore, US 200301:2003 6 Non-volatile memory device with impro  | 438/20 257/E29.1 | 438/20 257/E29.1 | <input checked="" type="checkbox"/> | US 200301 |   |
| 2  | <input checked="" type="checkbox"/> Nakazato, US 657414:2003 1 Memory device using hot charge carri     | 365/18 257/315   | 365/18 257/315   | <input checked="" type="checkbox"/> | US 657414 |   |
| 3  | <input checked="" type="checkbox"/> Rudeck, Pa US 200500:2005 2 Methods and structure for an improve    | 438/26 438/260   | 438/26 438/260   | <input checked="" type="checkbox"/> | US 200500 |   |
| 4  | <input checked="" type="checkbox"/> Chindalore, US 200401:2004 6 Non-volatile memory device with impro  | 257/32 257/321   | 257/32 257/321   | <input checked="" type="checkbox"/> | US 200401 |   |
| 5  | <input checked="" type="checkbox"/> Hyde, John US 200400:2004 3 Pseudo-nonvolatile direct-tunneling flo | 257/31 257/E29.3 | 257/31 257/E29.3 | <input checked="" type="checkbox"/> | US 200400 |   |
| 6  | <input checked="" type="checkbox"/> Forbes, Le US 200302:2003 2 Write once read only memory with larg   | 257/31 257/314   | 257/31 257/314   | <input checked="" type="checkbox"/> | US 200302 |   |
| 7  | <input checked="" type="checkbox"/> Rudeck, Pa US 200302:2003 2 Method and structure for an improved    | 438/20 257/E21.6 | 438/20 257/E21.6 | <input checked="" type="checkbox"/> | US 200302 |   |
| 8  | <input checked="" type="checkbox"/> Mihnea, An US 200300:2003 1 Flash memory cell for high efficiency p | 365/18 365/183.0 | 365/18 365/183.0 | <input checked="" type="checkbox"/> | US 200300 |   |
| 9  | <input checked="" type="checkbox"/> Mihnea, An US 200201:2002 1 Flash memory cell for high efficiency p | 257/31 257/E21.2 | 257/31 257/E21.2 | <input checked="" type="checkbox"/> | US 200201 |   |
| 10 | <input checked="" type="checkbox"/> Forbes, Le US 200201:2002 2 P-channel dynamic flash memory cells    |                  |                  | <input checked="" type="checkbox"/> |           |   |